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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	300
Number of Logic Elements/Cells	3840
Total RAM Bits	221184
Number of I/O	106
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	196-TFBGA, CSBGA
Supplier Device Package	196-CSPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc6slx4-2cpg196c

Table 3: **eFUSE Programming Conditions**(1)

Symbol	Description	Min	Typ	Max	Units
V_{FS}(2)	External voltage supply	3.2	3.3	3.4	V
I_{FS}	V_{FS} supply current	–	–	40	mA
V_{CCAUX}	Auxiliary supply voltage relative to GND	3.2	3.3	3.45	V
R_{FUSE}(3)	External resistor from R_{FUSE} pin to GND	1129	1140	1151	Ω
V_{CCINT}	Internal supply voltage relative to GND	1.14	1.2	1.26	V
t_j	Temperature range	15	–	85	°C

Notes:

1. These specifications apply during programming of the eFUSE AES key. Programming is only supported through JTAG.The AES key is only supported in the following devices: LX75, LX75T, LX100, LX100T, LX150, and LX150T.
2. When programming eFUSE, V_{FS} must be less than or equal to V_{CCAUX}. When not programming or when eFUSE is not used, Xilinx recommends connecting V_{FS} to GND. However, V_{FS} can be between GND and 3.45 V.
3. An R_{FUSE} resistor is required when programming the eFUSE AES key. When not programming or when eFUSE is not used, Xilinx recommends connecting the R_{FUSE} pin to V_{CCAUX} or GND. However, R_{FUSE} can be unconnected.

Table 4: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description		Min	Typ	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)		0.8	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)		2.0	–	–	V
I_{REF}	V_{REF} leakage current per pin for commercial (C) and industrial (I) devices		–10	–	10	μA
	V_{REF} leakage current per pin for expanded (Q) devices		–15	–	15	μA
I_L	Input or output leakage current per pin (sample-tested) for commercial (C) and industrial (I) devices		–10	–	10	μA
	Input or output leakage current per pin (sample-tested) for expanded (Q) devices		–15	–	15	μA
I_{HS}	Leakage current on pins during hot socketing with FPGA unpowered	All pins except PROGRAM_B, DONE, and JTAG pins when HSWAPEN = 1	–20	–	20	μA
		PROGRAM_B, DONE, and JTAG pins, or other pins when HSWAPEN = 0	I_{HS} + I_{RPU}			μA
C_{IN}(1)	Die input capacitance at the pad		–	–	10	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V or V_{CCAUX} = 3.3V		200	–	500	μA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V or V_{CCAUX} = 2.5V		120	–	350	μA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V		60	–	200	μA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V		40	–	150	μA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V		12	–	100	μA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = V_{CCO}, V_{CCAUX} = 3.3V		200	–	550	μA
	Pad pull-down (when selected) @ V_{IN} = V_{CCO}, V_{CCAUX} = 2.5V		140	–	400	μA
I_{BATT}(2)	Battery supply current		–	–	150	nA
R_{DT}(3)	Resistance of optional input differential termination circuit, V_{CCAUX} = 3.3V		–	100	–	Ω
R_{IN_TERM}(5)	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_25) for commercial (C) and industrial (I) devices		23	25	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_25) for expanded (Q) devices		20	25	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_50) for commercial (C) and industrial (I) devices		39	50	72	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_50) for expanded (Q) devices		32	50	74	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_75) for commercial (C) and industrial (I) devices		56	75	109	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_75) for expanded (Q) devices		47	75	115	Ω
R_{OUT_TERM}	Thevenin equivalent resistance of programmable output termination (UNTUNED_25)		11	25	52	Ω
	Thevenin equivalent resistance of programmable output termination (UNTUNED_50)		21	50	96	Ω
	Thevenin equivalent resistance of programmable output termination (UNTUNED_75)		29	75	145	Ω

Notes:

1. The C_{IN} measurement represents the die capacitance at the pad, not including the package.
2. Maximum value specified for worst case process at 25°C. LX75, LX75T, LX100, LX100T, LX150, and LX150T only.
3. Refer to IBIS models for R_{DT} variation and for values at V_{CCAUX} = 2.5V. IBIS values for R_{DT} are valid for all temperature ranges.
4. V_{CCO2} is not required for data retention. The minimum V_{CCO2} for power-on reset and configuration is 1.65V.
5. Termination resistance to a V_{CCO}/2 level.

SelectIO™ Interface DC Input and Output Levels

Table 7: **Recommended Operating Conditions for User I/Os Using Single-Ended Standards**

I/O Standard	V_{CCO} for Drivers(1)			V_{REF} for Inputs		
	V, Min	V, Nom	V, Max	V, Min	V, Nom	V, Max
LVTTL	3.0	3.3	3.45	V_{REF} is not used for these I/O standards		
LVCMOS33	3.0	3.3	3.45			
LVCMOS25	2.3	2.5	2.7			
LVCMOS18	1.65	1.8	1.95			
LVCMOS18_JEDEC	1.65	1.8	1.95			
LVCMOS15	1.4	1.5	1.6			
LVCMOS15_JEDEC	1.4	1.5	1.6			
LVCMOS12	1.1	1.2	1.3			
LVCMOS12_JEDEC	1.1	1.2	1.3			
PCI33_3(2)	3.0	3.3	3.45			
PCI66_3(2)	3.0	3.3	3.45			
I2C	2.7	3.0	3.45			
SMBUS	2.7	3.0	3.45			
SDIO	3.0	3.3	3.45			
MOBILE_DDR	1.7	1.8	1.9			
HSTL_I	1.4	1.5	1.6	0.68	0.75	0.9
HSTL_II	1.4	1.5	1.6	0.68	0.75	0.9
HSTL_III	1.4	1.5	1.6	–	0.9	–
HSTL_I_18	1.7	1.8	1.9	0.8	0.9	1.1
HSTL_II_18	1.7	1.8	1.9	–	0.9	–
HSTL_III_18	1.7	1.8	1.9	–	1.1	–
SSTL3_I	3.0	3.3	3.45	1.3	1.5	1.7
SSTL3_II	3.0	3.3	3.45	1.3	1.5	1.7
SSTL2_I	2.3	2.5	2.7	1.13	1.25	1.38
SSTL2_II	2.3	2.5	2.7	1.13	1.25	1.38
SSTL18_I	1.7	1.8	1.9	0.833	0.9	0.969
SSTL18_II	1.7	1.8	1.9	0.833	0.9	0.969
SSTL15_II	1.425	1.5	1.575	0.69	0.75	0.81

Notes:

1. V_{CCO} range required when using I/O standard for an output. Also required for MOBILE_DDR, PCI33_3, LVCMOS18_JEDEC, LVCMOS15_JEDEC, and LVCMOS12_JEDEC inputs, and for LVCMOS25 inputs when V_{CCAUX} = 3.3V.
2. For PCI systems, the transmitter and receiver should have common supplies for V_{CCO}.

eFUSE Read Endurance

Table 11 lists the minimum guaranteed number of read cycle operations for Device DNA and for the AES eFUSE key. For more information, see UG380: *Spartan-6 FPGA Configuration User Guide*.

Table 11: **eFUSE Read Endurance**

Symbol	Description	Speed Grade				Units (Min)
		-3	-3N	-2	-1L	
DNA_CYCLES	Number of DNA_PORT READ operations or JTAG ISC_DNA read command operations. Unaffected by SHIFT operations.	30,000,000				Read Cycles
AES_CYCLES	Number of JTAG FUSE_KEY or FUSE_CNTL read command operations. Unaffected by SHIFT operations.	30,000,000				Read Cycles

GTP Transceiver Specifications

GTP transceivers are available in the Spartan-6 LXT devices. See DS160: *Spartan-6 Family Overview* for more information.

GTP Transceiver DC Characteristics

Table 12: **Absolute Maximum Ratings for GTP Transceivers(1)**

Symbol	Description	MIn	Max	Units
MGTAVCC	Analog supply voltage for the GTP transmitter and receiver circuits relative to GND	–0.5	1.32	V
MGTAVTTTX	Analog supply voltage for the GTP transmitter termination circuit relative to GND	–0.5	1.32	V
MGTAVTTRX	Analog supply voltage for the GTP receiver termination circuit relative to GND	–0.5	1.32	V
MGTAVCCPLL	Analog supply voltage for the GTP transmitter and receiver PLL circuits relative to GND	–0.5	1.32	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTP transceiver bank (top or bottom)	–0.5	1.32	V
V_{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	–0.5	1.32	V
$V_{MGTREFCLK}$	Reference clock absolute input voltage	–0.5	1.32	V

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.

Table 13: **Recommended Operating Conditions for GTP Transceivers(1)(2)(3)**

Symbol	Description	Min	Typ	Max	Units
MGTAVCC	Analog supply voltage for the GTP transmitter and receiver circuits relative to GND	1.14	1.20	1.26	V
MGTAVTTTX	Analog supply voltage for the GTP transmitter termination circuit relative to GND	1.14	1.20	1.26	V
MGTAVTTRX	Analog supply voltage for the GTP receiver termination circuit relative to GND	1.14	1.20	1.26	V
MGTAVCCPLL	Analog supply voltage for the GTP transmitter and receiver PLL circuits relative to GND	1.14	1.20	1.26	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTP transceiver bank (top or bottom)	1.14	1.20	1.26	V

Notes:

1. Each voltage listed requires the filter circuit described in UG386: *Spartan-6 FPGA GTP Transceivers User Guide*.
2. Voltages are specified for the temperature range of T_j = –40°C to +125°C.
3. The voltage level of MGTAVCCPLL must not exceed the voltage level of MGTAVCC +10mV. The voltage level of MGTAVCC must not exceed the voltage level of MGTAVCCPLL.

Table 23: **GTP Transceiver Receiver Switching Characteristics**

Symbol	Description			Min	Typ	Max	Units
$T_{RXELECIDLE}$	Time for RXELECIDLE to respond to loss or restoration of data			–	75	–	ns
$R_{XOOBVDPP}$	OOB detect threshold peak-to-peak			60	–	150	mV
R_{XSST}	Receiver spread-spectrum tracking(1)		Modulated @ 33 KHz	–5000	–	0	ppm
R_{XRL}	Run length (CID)	Internal AC capacitor bypassed		–	–	150	UI
$R_{XPPMTOL}$	Data/REFCLK PPM offset tolerance	CDR 2nd-order loop disabled		–200	–	200	ppm
		CDR 2nd-order loop enabled	PLL_RXDIVSEL_OUT = 1	–2000	–	2000	ppm
			PLL_RXDIVSEL_OUT = 2	–2000	–	2000	ppm
			PLL_RXDIVSEL_OUT = 4	–1000	–	1000	ppm
SJ Jitter Tolerance(2)							
$JT\_SJ_{3.125}$	Sinusoidal Jitter(3)		3.125 Gb/s	0.4	–	–	UI
$JT\_SJ_{2.5}$	Sinusoidal Jitter(3)		2.5 Gb/s	0.4	–	–	UI
$JT\_SJ_{1.62}$	Sinusoidal Jitter(3)		1.62 Gb/s	0.5	–	–	UI
$JT\_SJ_{1.25}$	Sinusoidal Jitter(3)		1.25 Gb/s	0.5	–	–	UI
JT_SJ_{614}	Sinusoidal Jitter(3)		614 Mb/s	0.5	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)(5)							
$JT\_TJSE_{3.125}$	Total Jitter with stressed eye(4)		3.125 Gb/s	0.65	–	–	UI
$JT\_SJSE_{3.125}$	Sinusoidal Jitter with stressed eye		3.125 Gb/s	0.1	–	–	UI
$JT\_TJSE_{2.7}$	Total Jitter with stressed eye(4)		2.7 Gb/s	0.65	–	–	UI
$JT\_SJSE_{2.7}$	Sinusoidal Jitter with stressed eye		2.7 Gb/s	0.1	–	–	UI

Notes:

1. Using PLL_RXDIVSEL_OUT = 1, 2, and 4.
2. All jitter values are based on a Bit Error Ratio of $1e^{-12}$.
3. Using 80 MHz sinusoidal jitter only in the absence of deterministic and random jitter.
4. Composed of 0.37 UI DJ in the form of ISI and 0.18 UI RJ.
5. Measured using PRBS7 data pattern.

Endpoint Block for PCI Express Designs Switching Characteristics

The Endpoint block for PCI Express is available in the Spartan-6 LXT devices. Consult the Spartan-6 FPGA Integrated Endpoint Block for PCI Express for further information.

Table 24: **Maximum Performance for PCI Express Designs**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
$F_{PCIEUSER}$	User clock maximum frequency	62.5	62.5	62.5	N/A	MHz

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Spartan-6 devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the Switching Characteristics, page 19.

Table 25: **Interface Performances**

Description	I/O Resource	Clock Buffer	Data Width	Speed Grade				Units
				-3	-3N	-2	-1L	
Networking Applications(1)								
SDR LVDS transmitter or receiver	IOB SDR register	BUFG	–	400	400	375	250	Mb/s
DDR LVDS transmitter or receiver	ODDR2/IDDR2 register	2 BUFGs	–	800	800	750	500	Mb/s
SDR LVDS transmitter	OSERDES2	BUFPLL	2	500	500	500	250	Mb/s
			3	750	750	750	375	Mb/s
			4-8	1080	1050	950	500	Mb/s
DDR LVDS transmitter	OSERDES2	2 BUFIO2s	2	500	500	500	250	Mb/s
			3	750	750	750	375	Mb/s
			4-8	1080	1050	950	500	Mb/s
SDR LVDS receiver	ISERDES2 in RETIMED mode	BUFPLL	2	500	500	500	—	Mb/s
			3	750	750	750	—	Mb/s
			4-8	1080	1050	950	—	Mb/s
DDR LVDS receiver	ISERDES2 in RETIMED mode	2 BUFIO2s	2	500	500	500	—	Mb/s
			3	750	750	750	—	Mb/s
			4-8	1080	1050	950	—	Mb/s
Memory Interfaces (Implemented using the Spartan-6 FPGA Memory Controller Block)(2)								
Standard Performance (Standard V_{CCINT})								
DDR				400	Note 4	400	350	Mb/s
DDR2				667	Note 4	625	400	Mb/s
DDR3				800	Note 4	667	—	Mb/s
LPDDR (Mobile_DDR)				400	Note 4	400	350	Mb/s
Extended Performance (Requires Extended Performance V_{CCINT})(3)								
DDR2				800	Note 4	667	—	Mb/s

Notes:

1. Refer to XAPP1064, *Source-Synchronous Serialization and Deserialization (up to 1050 Mb/s)* and UG381, *Spartan-6 FPGA SelectIO Resources User Guide.*
2. Refer to UG388, *Spartan-6 FPGA Memory Controller User Guide*.
3. Extended Memory Controller block performance for DDR2 can be achieved using the extended performance V_{CCINT} range from Table 2.
4. The LX4 device, all devices in the TQG144 and CPG196 packages, and the -3N speed grade do not support a Memory Controller Block.

Switching Characteristics

All values represented in this data sheet are based on these speed specifications: v1.20 for -3, -3N, and -2; and v1.08 for -1L. Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Production

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to Production before faster speed grades.

All specifications are always representative of worst-case supply voltage and junction temperature conditions.

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device.

The -1L speed grade refers to the lower-power Spartan-6 devices. The -3N speed grade refers to the Spartan-6 devices that do not support MCB functionality.

Table 26 correlates the current status of each Spartan-6 device on a per speed grade basis.

Table 26: **Spartan-6 Device Speed Grade Designations**

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC6SLX4[1]			-3, -2, -1L
XC6SLX9			-3, -3N, -2, -1L
XC6SLX16			-3, -3N, -2, -1L
XC6SLX25			-3, -3N, -2, -1L
XC6SLX25T			-3, -3N, -2
XC6SLX45			-3, -3N, -2, -1L
XC6SLX45T			-3, -3N, -2
XC6SLX75			-3, -3N, -2, -1L
XC6SLX75T			-3, -3N, -2
XC6SLX100			-3, -3N, -2, -1L
XC6SLX100T			-3, -3N, -2
XC6SLX150			-3, -3N, -2, -1L
XC6SLX150T			-3, -3N, -2
XA6SLX4			-3, -2
XA6SLX9			-3, -2
XA6SLX16			-3, -2
XA6SLX25			-3, -2
XA6SLX25T			-3, -2
XA6SLX45			-3, -2
XA6SLX45T			-3, -2
XA6SLX75			-3, -2
XA6SLX75T			-3, -2
XA6SLX100			-2
XQ6SLX75			-2, -1L
XQ6SLX75T			-3, -2
XQ6SLX150			-2, -1L
XQ6SLX150T			-3, -2

Notes:

1. The XC6SLX4 is not available in the -3N speed grade.

Testing of Switching Characteristics

All devices are 100% functionally tested. Internal timing parameters are derived from measuring internal test patterns. Listed below are representative values.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Spartan-6 devices.

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	
PPDS_33	1.17	1.29	1.42	1.68	1.57	1.71	1.91	2.43	3000	3000	3000	3000	ns
PPDS_25	1.01	1.13	1.26	1.56	1.68	1.82	2.02	2.47	3000	3000	3000	3000	ns
PCI33_3	1.07	1.19	1.32	1.57(2)	3.51	3.65	3.85	4.38(2)	3.51	3.65	3.85	4.38(1)	ns
PCI66_3	1.07	1.19	1.32	1.57(2)	3.53	3.67	3.87	4.39(2)	3.53	3.67	3.87	4.39(1)	ns
DISPLAY_PORT	1.02	1.14	1.27	1.56	3.15	3.29	3.49	4.08	3.15	3.29	3.49	4.08	ns
I2C	1.33	1.45	1.58	1.82	11.56	11.70	11.90	12.52	11.56	11.70	11.90	12.52	ns
SMBUS	1.33	1.45	1.58	1.82	11.56	11.70	11.90	12.52	11.56	11.70	11.90	12.52	ns
SDIO	1.36	1.48	1.61	1.84	2.64	2.78	2.98	3.60	2.64	2.78	2.98	3.60	ns
MOBILE_DDR	0.94	1.06	1.19	1.43	2.35	2.49	2.69	3.31	2.35	2.49	2.69	3.31	ns
HSTL_I	0.90	1.02	1.15	1.39	1.66	1.80	2.00	2.62	1.66	1.80	2.00	2.62	ns
HSTL_II	0.91	1.03	1.16	1.40	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
HSTL_III	0.95	1.07	1.20	1.44	1.67	1.81	2.01	2.61	1.67	1.81	2.01	2.61	ns
HSTL_I _18	0.94	1.06	1.19	1.43	1.77	1.91	2.11	2.73	1.77	1.91	2.11	2.73	ns
HSTL_II _18	0.94	1.06	1.19	1.43	1.85	1.99	2.19	2.81	1.85	1.99	2.19	2.81	ns
HSTL_III _18	0.99	1.11	1.24	1.47	1.79	1.93	2.13	2.72	1.79	1.93	2.13	2.72	ns
SSTL3_I	1.58	1.70	1.83	2.16	1.83	1.97	2.17	2.72	1.83	1.97	2.17	2.72	ns
SSTL3_II	1.58	1.70	1.83	2.16	2.01	2.15	2.35	2.94	2.01	2.15	2.35	2.94	ns
SSTL2_I	1.30	1.42	1.55	1.87	1.77	1.91	2.11	2.69	1.77	1.91	2.11	2.69	ns
SSTL2_II	1.30	1.42	1.55	1.88	1.86	2.00	2.20	2.82	1.86	2.00	2.20	2.82	ns
SSTL18_I	0.92	1.04	1.17	1.41	1.63	1.77	1.97	2.59	1.63	1.77	1.97	2.59	ns
SSTL18_II	0.92	1.04	1.17	1.41	1.66	1.80	2.00	2.62	1.66	1.80	2.00	2.62	ns
SSTL15_II	0.92	1.04	1.17	1.41	1.67	1.81	2.01	2.63	1.67	1.81	2.01	2.63	ns
DIFF_HSTL_I	0.94	1.06	1.19	1.46	1.77	1.91	2.11	2.62	1.77	1.91	2.11	2.62	ns
DIFF_HSTL_II	0.93	1.05	1.18	1.45	1.72	1.86	2.06	2.54	1.72	1.86	2.06	2.54	ns
DIFF_HSTL_III	0.93	1.05	1.18	1.46	1.69	1.83	2.03	2.53	1.69	1.83	2.03	2.53	ns
DIFF_HSTL_I_18	0.97	1.09	1.22	1.50	1.79	1.93	2.13	2.63	1.79	1.93	2.13	2.63	ns
DIFF_HSTL_II_18	0.97	1.09	1.22	1.49	1.69	1.83	2.03	2.51	1.69	1.83	2.03	2.51	ns
DIFF_HSTL_III_18	0.97	1.09	1.22	1.50	1.69	1.83	2.03	2.53	1.69	1.83	2.03	2.53	ns
DIFF_SSTL3_I	1.18	1.30	1.43	1.68	1.81	1.95	2.15	2.64	1.81	1.95	2.15	2.64	ns
DIFF_SSTL3_II	1.19	1.31	1.44	1.68	1.80	1.94	2.14	2.63	1.80	1.94	2.14	2.63	ns
DIFF_SSTL2_I	1.02	1.14	1.27	1.57	1.80	1.94	2.14	2.62	1.80	1.94	2.14	2.62	ns
DIFF_SSTL2_II	1.02	1.14	1.27	1.57	1.76	1.90	2.10	2.57	1.76	1.90	2.10	2.57	ns
DIFF_SSTL18_I	0.97	1.09	1.22	1.51	1.72	1.86	2.06	2.56	1.72	1.86	2.06	2.56	ns
DIFF_SSTL18_II	0.98	1.10	1.23	1.50	1.68	1.82	2.02	2.52	1.68	1.82	2.02	2.52	ns
DIFF_SSTL15_II	0.94	1.06	1.19	1.46	1.67	1.81	2.01	2.50	1.67	1.81	2.01	2.50	ns
DIFF_MOBILE_DDR	0.97	1.09	1.22	1.51	1.75	1.89	2.09	2.57	1.75	1.89	2.09	2.57	ns

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	
LVCMOS18, Slow, 24 mA	1.18	1.30	1.43	2.04	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18, Fast, 2 mA	1.18	1.30	1.43	2.04	3.59	3.73	3.93	4.53	3.59	3.73	3.93	4.53	ns
LVCMOS18, Fast, 4 mA	1.18	1.30	1.43	2.04	2.39	2.53	2.73	3.35	2.39	2.53	2.73	3.35	ns
LVCMOS18, Fast, 6 mA	1.18	1.30	1.43	2.04	1.88	2.02	2.22	2.84	1.88	2.02	2.22	2.84	ns
LVCMOS18, Fast, 8 mA	1.18	1.30	1.43	2.04	1.81	1.95	2.15	2.77	1.81	1.95	2.15	2.77	ns
LVCMOS18, Fast, 12 mA	1.18	1.30	1.43	2.04	1.71	1.85	2.05	2.67	1.71	1.85	2.05	2.67	ns
LVCMOS18, Fast, 16 mA	1.18	1.30	1.43	2.04	1.71	1.85	2.05	2.67	1.71	1.85	2.05	2.67	ns
LVCMOS18, Fast, 24 mA	1.18	1.30	1.43	2.04	1.71	1.85	2.05	2.67	1.71	1.85	2.05	2.67	ns
LVCMOS18_JEDEC, QUIETIO, 2 mA	0.94	1.06	1.19	1.41	5.91	6.05	6.25	6.79	5.91	6.05	6.25	6.79	ns
LVCMOS18_JEDEC, QUIETIO, 4 mA	0.94	1.06	1.19	1.41	4.75	4.89	5.09	5.64	4.75	4.89	5.09	5.64	ns
LVCMOS18_JEDEC, QUIETIO, 6 mA	0.94	1.06	1.19	1.41	4.04	4.18	4.38	4.96	4.04	4.18	4.38	4.96	ns
LVCMOS18_JEDEC, QUIETIO, 8 mA	0.94	1.06	1.19	1.41	3.71	3.85	4.05	4.62	3.71	3.85	4.05	4.62	ns
LVCMOS18_JEDEC, QUIETIO, 12 mA	0.94	1.06	1.19	1.41	3.35	3.49	3.69	4.28	3.35	3.49	3.69	4.28	ns
LVCMOS18_JEDEC, QUIETIO, 16 mA	0.94	1.06	1.19	1.41	3.20	3.34	3.54	4.13	3.20	3.34	3.54	4.13	ns
LVCMOS18_JEDEC, QUIETIO, 24 mA	0.94	1.06	1.19	1.41	2.96	3.10	3.30	3.98	2.96	3.10	3.30	3.98	ns
LVCMOS18_JEDEC, Slow, 2 mA	0.94	1.06	1.19	1.41	4.59	4.73	4.93	5.54	4.59	4.73	4.93	5.54	ns
LVCMOS18_JEDEC, Slow, 4 mA	0.94	1.06	1.19	1.41	3.69	3.83	4.03	4.60	3.69	3.83	4.03	4.60	ns
LVCMOS18_JEDEC, Slow, 6 mA	0.94	1.06	1.19	1.41	3.00	3.14	3.34	3.94	3.00	3.14	3.34	3.94	ns
LVCMOS18_JEDEC, Slow, 8 mA	0.94	1.06	1.19	1.41	2.19	2.33	2.53	3.18	2.19	2.33	2.53	3.18	ns
LVCMOS18_JEDEC, Slow, 12 mA	0.94	1.06	1.19	1.41	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18_JEDEC, Slow, 16 mA	0.94	1.06	1.19	1.41	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18_JEDEC, Slow, 24 mA	0.94	1.06	1.19	1.41	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18_JEDEC, Fast, 2 mA	0.94	1.06	1.19	1.41	3.57	3.71	3.91	4.52	3.57	3.71	3.91	4.52	ns
LVCMOS18_JEDEC, Fast, 4 mA	0.94	1.06	1.19	1.41	2.39	2.53	2.73	3.35	2.39	2.53	2.73	3.35	ns
LVCMOS18_JEDEC, Fast, 6 mA	0.94	1.06	1.19	1.41	1.88	2.02	2.22	2.84	1.88	2.02	2.22	2.84	ns
LVCMOS18_JEDEC, Fast, 8 mA	0.94	1.06	1.19	1.41	1.80	1.94	2.14	2.76	1.80	1.94	2.14	2.76	ns
LVCMOS18_JEDEC, Fast, 12 mA	0.94	1.06	1.19	1.41	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
LVCMOS18_JEDEC, Fast, 16 mA	0.94	1.06	1.19	1.41	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
LVCMOS18_JEDEC, Fast, 24 mA	0.94	1.06	1.19	1.41	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
LVCMOS15, QUIETIO, 2 mA	0.98	1.10	1.23	1.79	5.47	5.61	5.81	6.38	5.47	5.61	5.81	6.38	ns
LVCMOS15, QUIETIO, 4 mA	0.98	1.10	1.23	1.79	4.61	4.75	4.95	5.51	4.61	4.75	4.95	5.51	ns
LVCMOS15, QUIETIO, 6 mA	0.98	1.10	1.23	1.79	4.07	4.21	4.41	4.97	4.07	4.21	4.41	4.97	ns
LVCMOS15, QUIETIO, 8 mA	0.98	1.10	1.23	1.79	3.91	4.05	4.25	4.81	3.91	4.05	4.25	4.81	ns
LVCMOS15, QUIETIO, 12 mA	0.98	1.10	1.23	1.79	3.53	3.67	3.87	4.51	3.53	3.67	3.87	4.51	ns
LVCMOS15, QUIETIO, 16 mA	0.98	1.10	1.23	1.79	3.32	3.46	3.66	4.31	3.32	3.46	3.66	4.31	ns
LVCMOS15, Slow, 2 mA	0.98	1.10	1.23	1.79	4.18	4.32	4.52	5.11	4.18	4.32	4.52	5.11	ns
LVCMOS15, Slow, 4 mA	0.98	1.10	1.23	1.79	3.42	3.56	3.76	4.34	3.42	3.56	3.76	4.34	ns
LVCMOS15, Slow, 6 mA	0.98	1.10	1.23	1.79	2.29	2.43	2.63	3.24	2.29	2.43	2.63	3.24	ns

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices** ***(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	
LVCMOS15, Slow, 8 mA	0.98	1.10	1.23	1.79	2.30	2.44	2.64	3.25	2.30	2.44	2.64	3.25	ns
LVCMOS15, Slow, 12 mA	0.98	1.10	1.23	1.79	2.03	2.17	2.37	2.99	2.03	2.17	2.37	2.99	ns
LVCMOS15, Slow, 16 mA	0.98	1.10	1.23	1.79	2.01	2.15	2.35	2.97	2.01	2.15	2.35	2.97	ns
LVCMOS15, Fast, 2 mA	0.98	1.10	1.23	1.79	3.29	3.43	3.63	4.24	3.29	3.43	3.63	4.24	ns
LVCMOS15, Fast, 4 mA	0.98	1.10	1.23	1.79	2.27	2.41	2.61	3.22	2.27	2.41	2.61	3.22	ns
LVCMOS15, Fast, 6 mA	0.98	1.10	1.23	1.79	1.78	1.92	2.12	2.74	1.78	1.92	2.12	2.74	ns
LVCMOS15, Fast, 8 mA	0.98	1.10	1.23	1.79	1.73	1.87	2.07	2.69	1.73	1.87	2.07	2.69	ns
LVCMOS15, Fast, 12 mA	0.98	1.10	1.23	1.79	1.73	1.87	2.07	2.64	1.73	1.87	2.07	2.64	ns
LVCMOS15, Fast, 16 mA	0.98	1.10	1.23	1.79	1.73	1.87	2.07	2.64	1.73	1.87	2.07	2.64	ns
LVCMOS15_JEDEC, QUIETIO, 2 mA	1.03	1.15	1.28	1.49	5.49	5.63	5.83	6.37	5.49	5.63	5.83	6.37	ns
LVCMOS15_JEDEC, QUIETIO, 4 mA	1.03	1.15	1.28	1.49	4.61	4.75	4.95	5.51	4.61	4.75	4.95	5.51	ns
LVCMOS15_JEDEC, QUIETIO, 6 mA	1.03	1.15	1.28	1.49	4.07	4.21	4.41	4.97	4.07	4.21	4.41	4.97	ns
LVCMOS15_JEDEC, QUIETIO, 8 mA	1.03	1.15	1.28	1.49	3.92	4.06	4.26	4.81	3.92	4.06	4.26	4.81	ns
LVCMOS15_JEDEC, QUIETIO, 12 mA	1.03	1.15	1.28	1.49	3.54	3.68	3.88	4.51	3.54	3.68	3.88	4.51	ns
LVCMOS15_JEDEC, QUIETIO, 16 mA	1.03	1.15	1.28	1.49	3.33	3.47	3.67	4.31	3.33	3.47	3.67	4.31	ns
LVCMOS15_JEDEC, Slow, 2 mA	1.03	1.15	1.28	1.49	4.18	4.32	4.52	5.13	4.18	4.32	4.52	5.13	ns
LVCMOS15_JEDEC, Slow, 4 mA	1.03	1.15	1.28	1.49	3.42	3.56	3.76	4.35	3.42	3.56	3.76	4.35	ns
LVCMOS15_JEDEC, Slow, 6 mA	1.03	1.15	1.28	1.49	2.29	2.43	2.63	3.25	2.29	2.43	2.63	3.25	ns
LVCMOS15_JEDEC, Slow, 8 mA	1.03	1.15	1.28	1.49	2.30	2.44	2.64	3.26	2.30	2.44	2.64	3.26	ns
LVCMOS15_JEDEC, Slow, 12 mA	1.03	1.15	1.28	1.49	2.01	2.15	2.35	2.97	2.01	2.15	2.35	2.97	ns
LVCMOS15_JEDEC, Slow, 16 mA	1.03	1.15	1.28	1.49	2.01	2.15	2.35	2.97	2.01	2.15	2.35	2.97	ns
LVCMOS15_JEDEC, Fast, 2 mA	1.03	1.15	1.28	1.49	3.28	3.42	3.62	4.22	3.28	3.42	3.62	4.22	ns
LVCMOS15_JEDEC, Fast, 4 mA	1.03	1.15	1.28	1.49	2.27	2.41	2.61	3.23	2.27	2.41	2.61	3.23	ns
LVCMOS15_JEDEC, Fast, 6 mA	1.03	1.15	1.28	1.49	1.78	1.92	2.12	2.74	1.78	1.92	2.12	2.74	ns
LVCMOS15_JEDEC, Fast, 8 mA	1.03	1.15	1.28	1.49	1.73	1.87	2.07	2.69	1.73	1.87	2.07	2.69	ns
LVCMOS15_JEDEC, Fast, 12 mA	1.03	1.15	1.28	1.49	1.73	1.87	2.07	2.63	1.73	1.87	2.07	2.63	ns
LVCMOS15_JEDEC, Fast, 16 mA	1.03	1.15	1.28	1.49	1.73	1.87	2.07	2.63	1.73	1.87	2.07	2.63	ns
LVCMOS12, QUIETIO, 2 mA	0.91	1.03	1.16	1.51	6.40	6.54	6.74	7.30	6.40	6.54	6.74	7.30	ns
LVCMOS12, QUIETIO, 4 mA	0.91	1.03	1.16	1.51	4.98	5.12	5.32	5.90	4.98	5.12	5.32	5.90	ns
LVCMOS12, QUIETIO, 6 mA	0.91	1.03	1.16	1.51	4.65	4.79	4.99	5.55	4.65	4.79	4.99	5.55	ns
LVCMOS12, QUIETIO, 8 mA	0.91	1.03	1.16	1.51	4.23	4.37	4.57	5.21	4.23	4.37	4.57	5.21	ns
LVCMOS12, QUIETIO, 12 mA	0.91	1.03	1.16	1.51	3.98	4.12	4.32	4.94	3.98	4.12	4.32	4.94	ns
LVCMOS12, Slow, 2 mA	0.91	1.03	1.16	1.51	4.98	5.12	5.32	5.91	4.98	5.12	5.32	5.91	ns
LVCMOS12, Slow, 4 mA	0.91	1.03	1.16	1.51	2.84	2.98	3.18	3.81	2.84	2.98	3.18	3.81	ns
LVCMOS12, Slow, 6 mA	0.91	1.03	1.16	1.51	2.77	2.91	3.11	3.72	2.77	2.91	3.11	3.72	ns
LVCMOS12, Slow, 8 mA	0.91	1.03	1.16	1.51	2.34	2.48	2.68	3.31	2.34	2.48	2.68	3.31	ns
LVCMOS12, Slow, 12 mA	0.91	1.03	1.16	1.51	2.08	2.22	2.42	3.06	2.08	2.22	2.42	3.06	ns

Table 32: **Output Delay Measurement Methodology *(Cont'd)***

Description	I/O Standard Attribute	R_{REF} (Ω)	C_{REF}[1] (pF)	V_{MEAS} (V)	V_{REF} (V)
SSTL, Class II, 2.5V	SSTL2_II	25	0	V_{REF}	1.25
SSTL, Class II, 1.5V	SSTL15_II	25	0	V_{REF}	0.75
LVDS (Low-Voltage Differential Signaling), 2.5V & 3.3V	LVDS_25, LVDS_33	100	0	0(3)	–
BLVDS (Bus LVDS), 2.5V	BLVDS_25	Note 4	0	0(3)	–
Mini-LVDS, 2.5V & 3.3V	MINI_LVDS_25, MINI_LVDS_33	100	0	0(3)	–
RSDS (Reduced Swing Differential Signaling), 2.5V & 3.3V	RSDS_25, RSDS_33	100	0	0(3)	–
TMDS (Transition Minimized Differential Signaling), 3.3V	TMDS_33	Note 5	0	0(3)	–
PPDS (Point-to-Point Differential Signaling, 2.5V & 3.3V	PPDS_25, PPDS_33	100	0	0(3)	–

Notes:

1. C_{REF} is the capacitance of the probe, nominally 0 pF.
2. Per PCI specifications.
3. The value given is the differential output voltage.
4. See the *BLVDS Output Termination* section in UG381, *Spartan-6 FPGA SelectIO Resources User Guide.*
5. See the *TMDS_33 Termination* section in UG381, *Spartan-6 FPGA SelectIO Resources User Guide.*

Simultaneously Switching Outputs

Due to package electrical parasitics, a given package supports a limited number of simultaneous switching outputs (SSOs) when using fast, high-drive outputs. Table 33 and Table 34 provide guidelines for the recommended maximum allowable number of SSOs. These guidelines describe the maximum number of user I/O pins of an output signal standard that should simultaneously switch in the same direction, while maintaining a safe level of switching noise for that particular signal standard. Meeting these guidelines for the stated test conditions ensures that the FPGA operates free from the adverse effects of GND and power bounce.

For each device/package combination, Table 33 provides the number of equivalent V_{CCO}/GND pairs per bank. For each output signal standard and drive strength, Table 34 recommends the maximum number of SSOs, switching in the same direction, allowed per V_{CCO}/GND pair within an I/O bank. The guidelines are categorized by package style, slew rate, and output drive current. The number of SSOs are also specified by I/O bank. Multiply the appropriate numbers from each table to calculate the maximum number of SSOs allowed within an I/O bank. The guidelines assume that all pins within a bank use the same I/O standard. Exceeding these SSO guidelines can result in increased power or GND bounce, degraded signal integrity, or increased system jitter. For a given I/O standard, if the SSO limit per pair in Table 34 is greater than the maximum I/O per pair in Table 33, then there is no SSO limit for the exclusive use of that I/O standard.

The recommended maximum SSO values assume that the FPGA is soldered on a printed circuit board and that the board uses sound design practices. Due to the additional inductance introduced by the socket, the SSO values do not apply for FPGAs mounted in sockets. The SSO values assume that the V_{CCAUX} is powered at 3.3V. Setting V_{CCAUX} to 2.5V provides better SSO characteristics. For more detail, see UG381: *Spartan-6 FPGA SelectIO Resources User Guide.*

Table 34: **SSO Limit per V_{CCO}/GND Pair**

V_{CCO}	I/O Standard	Drive	Slew	SSO Limit per V_{CCO}/GND Pair			
				All TQG144, CPG196, CSG225, FT(G)256, and LX devices in CSG324		All CS(G)484, FG(G)484, FG(G)676, FG(G)900, and LXT devices in CSG324	
				Bank 0/2	Bank 1/3	Bank 0/2	Bank 1/3/4/5
1.2V	LVCMOS12, LVCMOS12_JEDEC	2	Fast	30 (1)	35	30	35
			Slow	51	55	51	52
			QuietIO	71	58	71	70
		4	Fast	17	17	17	19
			Slow	23	25	23	22
			QuietIO	35	32	35	32
		6	Fast	13	15	13	14
			Slow	19	20	19	17
			QuietIO	26	24	26	24
		8	Fast	N/A	12	N/A	12
			Slow	N/A	15	N/A	13
			QuietIO	N/A	20	N/A	19
		12	Fast	N/A	5	N/A	4
			Slow	N/A	8	N/A	5
			QuietIO	N/A	11	N/A	10

Table 34: **SSO Limit per V_{CCO}/GND Pair *(Cont'd)***

V_{CCO}	I/O Standard	Drive	Slew	SSO Limit per V_{CCO}/GND Pair			
				All TQG144, CPG196, CSG225, FT(G)256, and LX devices in CSG324		All CS(G)484, FG(G)484, FG(G)676, FG(G)900, and LXT devices in CSG324	
				Bank 0/2	Bank 1/3	Bank 0/2	Bank 1/3/4/5
1.8V	LVCMOS18, LVCMOS18_JEDEC	2	Fast	39	46	39	47
			Slow	65	75	65	74
			QuietIO	80	80	80	85
		4	Fast	22	25	22	25
			Slow	38	36	38	29
			QuietIO	45	40	45	35
		6	Fast	16	18	16	17
			Slow	27	25	27	19
			QuietIO	30	28	30	23
		8	Fast	13	15	13	14
			Slow	16	18	16	16
			QuietIO	25	22	25	18
		12	Fast	5	7	5	5
			Slow	7	8	7	6
			QuietIO	11	10	11	8
		16	Fast	4	5	4	4
			Slow	7	8	7	5
			QuietIO	11	10	11	8
		24	Fast	N/A	5	N/A	3
			Slow	N/A	8	N/A	8
			QuietIO	N/A	10	N/A	8
	HSTL_I_18			9	10	9	9
	HSTL_II_18			N/A	5	N/A	6
	HSTL_III_18			9	10	9	11
	DIFF_HSTL_I_18			27	30	27	27
	DIFF_HSTL_II_18			N/A	15	N/A	18
	DIFF_HSTL_III_18			27	30	27	33
	MOBILE_DDR (3)			12	14	12	14
	DIFF_MOBILE_DDR (3)			36	42	36	42
	SSTL_18_I (3)			9	10	9	10
	SSTL_18_II (3)			N/A	5	N/A	4
	DIFF_SSTL_18_I (3)			27	30	27	30
	DIFF_SSTL_18_II (3)			N/A	15	N/A	12

Input/Output Logic Switching Characteristics

Table 35: **ILOGIC2 Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
Setup/Hold						
T_{ICE0CK}/T_{ICKCE0}	CE0 pin Setup/Hold with respect to CLK	0.56/ –0.30	0.56/ –0.25	0.79/ –0.22	1.21/ –0.52	ns
T_{ISRCK}/T_{ICKSR}	SR pin Setup/Hold with respect to CLK	0.74/ –0.23	0.74/ –0.22	0.98/ –0.20	1.31/ –0.45	ns
T_{IDOCK}/T_{IOCKD}	D pin Setup/Hold with respect to CLK without Delay	1.19/ –0.83	1.36/ –0.83	1.73/ –0.83	2.18/ –1.77	ns
T_{IDOCKD}/T_{IOCKDD}	DDLY pin Setup/Hold with respect to CLK (using IODELAY2)	0.31/ 0.00	0.47/ 0.00	0.54/ 0.00	0.63/ –0.39	ns
Combinatorial						
T_{IDI}	D pin to O pin propagation delay, no Delay	0.95	1.28	1.53	2.25	ns
T_{IDID}	DDLY pin to O pin propagation delay (using IODELAY2)	0.23	0.39	0.44	0.74	ns
Sequential Delays						
T_{IDLO}	D pin to Q pin using flip-flop as a latch without Delay	1.56	1.86	2.39	3.49	ns
T_{IDLOD}	DDLY pin to Q1 pin using flip-flop as a latch (using IODELAY2)	0.68	0.97	1.20	1.94	ns
T_{ICKQ}	CLK to Q outputs for XC devices	1.03	1.24	1.43	2.11	ns
	CLK to Q outputs for XA and XQ devices	1.38	N/A	1.78	2.11	ns
$T_{RQ\_ILOGIC2}$	SR pin to Q outputs	1.81	1.81	2.50	3.05	ns

Table 36: **OLOGIC2 Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
Setup/Hold						
T_{ODCK}/T_{OCKD}	D1/D2 pins Setup/Hold with respect to CLK	0.81/ –0.05	0.86/ –0.05	1.18/ 0.00	1.73/ –0.27	ns
T_{OOCECK}/T_{OCKOCE}	OCE pin Setup/Hold with respect to CLK	0.75/ –0.10	0.75/ –0.10	1.01/ –0.05	1.66/ –0.23	ns
T_{OSRCK}/T_{OCKSR}	SR pin Setup/Hold with respect to CLK	0.70/ –0.28	0.79/ –0.28	1.03/ –0.23	1.39/ –0.47	ns
T_{OTCK}/T_{OCKT}	T1/T2 pins Setup/Hold with respect to CLK	0.24/ –0.08	0.56/ –0.06	0.83/ –0.01	0.99/ –0.19	ns
T_{OTCECK}/T_{OCKTCE}	TCE pin Setup/Hold with respect to CLK	0.58/ –0.06	0.72/ –0.06	1.18/ –0.01	1.51/ –0.13	ns
Sequential Delays						
T_{OCKQ}	CLK to OQ/TQ out for XC devices	0.48	0.51	0.74	0.74	ns
	CLK to OQ/TQ out for XA and XQ devices	0.85	N/A	1.16	0.74	ns
$T_{RQ\_OLOGIC2}$	SR pin to OQ/TQ out	1.81	1.81	2.50	3.05	ns

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 41: **CLB Distributed RAM Switching Characteristics (SLICEM Only)**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
Sequential Delays						
T_{SHCKO}	Clock to A – D outputs	1.26	1.55	1.55	2.35	ns, Max
	Clock to A – D outputs (direct output path)	0.96	1.20	1.20	1.87	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{DS}/T_{DH}	AX – DX or AI – DI inputs to CLK	0.59/ 0.17	0.73/ 0.22	0.73/ 0.22	1.17/ 0.33	ns, Min
T_{AS}/T_{AH}	Address An inputs to clock for XC devices	0.28/ 0.35	0.32/ 0.42	0.32/ 0.42	0.26/ 0.71	ns, Min
	Address An inputs to clock for XA and XQ devices	0.28/ 0.51	N/A	0.32/ 0.51	0.26/ 0.71	ns, Min
T_{WS}/T_{WH}	WE input to clock	0.31/ –0.08	0.37/ –0.08	0.37/ –0.08	0.59/ –0.27	ns, Min
T_{CECK}/T_{CKCE}	CE input to CLK	0.31/ –0.08	0.37/ –0.08	0.37/ –0.08	0.59/ –0.27	ns, Min

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 42: **CLB Shift Register Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
Sequential Delays						
T_{REG}	Clock to A – D outputs	1.35	1.78	1.78	2.74	ns, Max
	Clock to A – D outputs (direct output path)	1.24	1.65	1.65	2.48	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{WS}/T_{WH}	WE input to CLK	0.20/ –0.07	0.24/ –0.07	0.24/ –0.07	0.29/ –0.27	ns, Min
T_{CECK}/T_{CKCE}	CE input to CLK for XC devices	0.30/ 0.30	0.30/ 0.38	0.30/ 0.38	0.82/ –0.41	ns, Min
	CE input to CLK for XA and XQ devices	0.32/ 0.30	N/A	0.40/ 0.38	0.82/ –0.41	ns, Min
T_{DS}/T_{DH}	AX – DX or AI – DI inputs to CLK	0.07/ 0.11	0.09/ 0.14	0.09/ 0.14	0.11/ 0.23	ns, Min

Table 47: Configuration Switching Characteristics(1) *(Cont'd)*

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
BPI Master Flash Mode Programming Switching(4)						
T_{BPICCO}(5)	A[25:0], FCS_B, FOE_B, FWE_B, LDC outputs valid after CCLK falling edge	15	15	15	20	ns, Max
$T_{BPIICCK}$	Master BPI CCLK (output) delay	10/100	10/100	10/100	10/130	µs, Min/Max
T_{BPIDCC}/T_{BPICCD}	Setup/Hold on D[15:0] data input pins	5.0/1.0	5.0/1.0	5.0/1.0	6.0/2.0	ns, Min
SPI Master Flash Mode Programming Switching(6)						
$T_{SPIDCC}/T_{SPIDCCD}$	DIN, MISO0, MISO1, MISO2, MISO3, Setup/Hold before/after the rising CCLK edge	5.0/1.0	5.0/1.0	5.0/1.0	7.0/1.0	ns, Min
$T_{SPIICCK}$	Master SPI CCLK (output) delay	0.4/7.0	0.4/7.0	0.4/7.0	0.4/10.0	µs, Min/Max
T_{SPICCM}	MOSI clock to out	13	13	13	19	ns, Max
$T_{SPICCFC}$	CSO_B clock to out	16	16	16	26	ns, Max
CCLK Output (Master Modes)						
T_{MCCKL}	Master CCLK clock duty cycle Low	40/60				%, Min/Max
T_{MCCKH}	Master CCLK clock duty cycle High	40/60				%, Min/Max
F_{MCCK}	Maximum frequency, serial mode (Master Serial/SPI) All devices	40	40	40	30	MHz, Max
	Maximum frequency, parallel mode (Master SelectMAP/BPI) LX9, LX16, LX25, LX25T, LX45, LX45T, LX75, and LX75T	40	40	40	25	MHz, Max
	Maximum frequency, parallel mode (Master SelectMAP/BPI) LX100 and LX100T in x8 mode, LX150, and LX150T	40	40	40	20	MHz, Max
	Maximum frequency, parallel mode (Master SelectMAP/BPI) LX100 and LX100T in x16 mode	35	35	35	20	MHz, Max
$F_{MCCKTOL}$	Frequency Tolerance, master mode	±50	±50	±50	±50	%
CCLK Input (Slave Modes)						
T_{SCCKL}	Slave CCLK clock minimum Low time	5	5	5	8	ns, Min
T_{SCCKH}	Slave CCLK clock minimum High time	5	5	5	8	ns, Min
USERCCLK Input						
$T_{USERCCLKL}$	USERCCLK clock minimum Low time	12	12	12	16	ns, Min
$T_{USERCCLKH}$	USERCCLK clock minimum High time	12	12	12	16	ns, Min
$F_{USERCCLK}$	Maximum USERCCLK frequency	40	40	40	30	MHz, Max

Notes:

1. Maximum frequency and setup/hold timing parameters are for 3.3V and 2.5V configuration voltages.
2. To support longer delays in configuration, use the design solutions described in UG380: *Spartan-6 FPGA Configuration User Guide*.
3. Table 6 specifies the power supply ramp time.
4. BPI mode is not supported in:
    - LX4, LX25, or LX25T devices
    - LX9 devices in the TQG144 package
    - LX9 or LX16 devices in the CPG196 package.
5. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.
6. Defense-grade Spartan-6Q -2Q devices configure in single default SPI Master (x1) mode at T_j = –55°C. During operation and when using all other configuration functions, the minimum operating temperature is –40°C.

Table 54: Switching Characteristics for the Delay-Locked Loop (DLL)[1] *(Cont'd)*

Symbol	Description	Speed Grade								Units
		-3		-3N		-2		-1L		
		Min	Max	Min	Max	Min	Max	Min	Max	
LOCK_DLL[3]	When using the DLL alone: The time from deassertion at the DCM's reset input to the rising transition at its LOCKED output. When the DCM is locked, the CLKIN and CLKFB signals are in phase. CLKIN_FREQ_DLL < 50 MHz.	–	5	–	5	–	5	–	5	ms
	When using the DLL alone: The time from deassertion at the DCM's reset input to the rising transition at its LOCKED output. When the DCM is locked, the CLKIN and CLKFB signals are in phase. CLKIN_FREQ_DLL > 50 MHz	–	0.60	–	0.60	–	0.60	–	0.60	ms
Delay Lines										
DCM_DELAY_STEP[5]	Finest delay resolution, averaged over all steps.	10	40	10	40	10	40	10	40	ps

Notes:

1. The values in this table are based on the operating conditions described in Table 2 and Table 53.
2. Indicates the maximum amount of output jitter that the DCM adds to the jitter on the CLKIN input.
3. For optimal jitter tolerance and faster LOCK time, use the CLKIN_PERIOD attribute.
4. Some jitter and duty-cycle specifications include 1% of input clock period or 0.01 UI. For example, this data sheet specifies a maximum jitter of ±(1% of CLKIN period + 150 ps). Assuming that the CLKIN frequency is 100 MHz, the equivalent CLKIN period is 10 ns. Since 1% of 10 ns is 0.1 ns or 100 ps, the maximum jitter is ±(100 ps + 150 ps) = ±250 ps.
5. A typical delay step size is 23 ps.
6. The timing analysis tools use the CLK_FEEDBACK = 1X condition for the CLKIN_CLKFB_PHASE value (reported as phase error). When using CLK_FEEDBACK = 2X, add 100 ps to the phase error for the CLKIN_CLKFB_PHASE value (as shown in this table).

Table 55: Recommended Operating Conditions for the Digital Frequency Synthesizer (DFS)[1]

Symbol	Description	Speed Grade								Units
		-3		-3N		-2		-1L		
		Min	Max	Min	Max	Min	Max	Min	Max	
Input Frequency Ranges[2]										
CLKIN_FREQ_FX	Frequency for the CLKIN input. Also described as F_{CLKIN}.	0.5	375[3]	0.5	375[3]	0.5	333[3]	0.5	200[3]	MHz
Input Clock Jitter Tolerance[4]										
CLKIN_CYC_JITT_FX_LF	Cycle-to-cycle jitter at the CLKIN input, based on CLKFX output frequency: FCLKFX < 150 MHz.	–	±300	–	±300	–	±300	–	±300	ps
CLKIN_CYC_JITT_FX_HF	Cycle-to-cycle jitter at the CLKIN input, based on CLKFX output frequency: FCLKFX > 150 MHz.	–	±150	–	±150	–	±150	–	±150	ps
CLKIN_PER_JITT_FX	Period jitter at the CLKIN input.	–	±1	–	±1	–	±1	–	±1	ns

Notes:

1. DFS specifications apply when using either of the DFS outputs (CLKFX or CLKFX180).
2. When using both DFS and DLL outputs on the same DCM, follow the more restrictive CLKIN_FREQ_DLL specifications in Table 53.
3. The CLKIN_DIVIDE_BY_2 attribute increases the effective input frequency range. When set to TRUE, the input clock frequency is divided by two as it enters the DCM. Input clock frequencies for the clock buffer being used can be increased up to the F_{MAX} (see Table 48 and Table 49 for BUFG and BUFIO2 limits).
4. CLKIN input jitter beyond these limits can cause the DCM to lose LOCK.

Table 66: **Global Clock Input to Output Delay With PLL in System-Synchronous Mode**

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
LVCMOS25 Global Clock Input to Output Delay using Output Flip-Flop, 12mA, Fast Slew Rate, *with* PLL in System-Synchronous Mode.							
$T_{ICKOFPLL}$	Global Clock and OUTFF *with* PLL	XC6SLX4	4.57	N/A	6.25	7.34	ns
		XC6SLX9	4.57	5.25	6.25	7.34	ns
		XC6SLX16	4.41	4.64	5.39	6.92	ns
		XC6SLX25	4.03	4.32	4.91	7.64	ns
		XC6SLX25T	4.03	4.32	4.91	N/A	ns
		XC6SLX45	4.63	4.96	5.75	7.36	ns
		XC6SLX45T	4.63	4.96	5.75	N/A	ns
		XC6SLX75	4.01	4.30	4.88	7.15	ns
		XC6SLX75T	4.01	4.30	4.88	N/A	ns
		XC6SLX100	4.02	4.33	4.90	7.37	ns
		XC6SLX100T	4.06	4.33	4.90	N/A	ns
		XC6SLX150	3.65	3.98	4.58	6.94	ns
		XC6SLX150T	3.65	3.98	4.58	N/A	ns
		XA6SLX4	4.88	N/A	6.13	N/A	ns
		XA6SLX9	4.88	N/A	6.13	N/A	ns
		XA6SLX16	4.74	N/A	5.27	N/A	ns
		XA6SLX25	4.43	N/A	4.78	N/A	ns
		XA6SLX25T	4.43	N/A	4.88	N/A	ns
		XA6SLX45	4.94	N/A	5.62	N/A	ns
		XA6SLX45T	4.94	N/A	5.62	N/A	ns
		XA6SLX75	4.32	N/A	4.77	N/A	ns
		XA6SLX75T	4.32	N/A	4.77	N/A	ns
		XA6SLX100	N/A	N/A	5.41	N/A	ns
		XQ6SLX75	N/A	N/A	4.77	7.15	ns
		XQ6SLX75T	4.32	N/A	4.77	N/A	ns
		XQ6SLX150	N/A	N/A	4.60	6.94	ns
		XQ6SLX150T	4.35	N/A	4.60	N/A	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. PLL output jitter is included in the timing calculation.

Table 74: **Global Clock Setup and Hold With PLL in System-Synchronous Mode**

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for LVCMOS25 Standard.[1]							
T_{PSPLL}/ T_{PHPLL}	No Delay Global Clock and IFF[2] with PLL in System-Synchronous Mode	XC6SLX4	1.37/0.25	N/A	1.52/0.41	2.07/0.69	ns
		XC6SLX9	1.37/0.21	1.48/0.21	1.52/0.26	2.07/0.69	ns
		XC6SLX16	1.33/–0.03	1.53/–0.02	1.60/–0.02	1.57/0.48	ns
		XC6SLX25	1.65/0.28	1.71/0.28	1.91/0.28	2.44/0.76	ns
		XC6SLX25T	1.65/0.28	1.71/0.28	1.91/0.28	N/A	ns
		XC6SLX45	1.55/0.18	1.64/0.18	1.75/0.18	2.02/0.90	ns
		XC6SLX45T	1.55/0.18	1.64/0.18	1.75/0.18	N/A	ns
		XC6SLX75	1.77/0.21	1.89/0.21	2.13/0.21	2.46/0.53	ns
		XC6SLX75T	1.77/0.21	1.89/0.21	2.13/0.21	N/A	ns
		XC6SLX100	1.44/0.32	1.52/0.32	1.70/0.32	1.78/0.86	ns
		XC6SLX100T	1.44/0.32	1.52/0.32	1.70/0.32	N/A	ns
		XC6SLX150	1.39/0.49	1.48/0.49	1.67/0.49	1.94/0.94	ns
		XC6SLX150T	1.39/0.49	1.48/0.49	1.67/0.49	N/A	ns
		XA6SLX4	1.61/0.10	N/A	1.64/0.28	N/A	ns
		XA6SLX9	1.61/0.10	N/A	1.64/0.28	N/A	ns
		XA6SLX16	1.89/–0.08	N/A	1.72/–0.08	N/A	ns
		XA6SLX25	1.85/0.16	N/A	2.08/0.16	N/A	ns
		XA6SLX25T	1.85/0.16	N/A	2.17/0.16	N/A	ns
		XA6SLX45	1.58/0.07	N/A	1.87/0.03	N/A	ns
		XA6SLX45T	1.58/0.07	N/A	1.87/0.03	N/A	ns
		XA6SLX75	1.80/0.06	N/A	2.25/0.06	N/A	ns
		XA6SLX75T	1.80/0.06	N/A	2.25/0.06	N/A	ns
		XA6SLX100	N/A	N/A	2.34/0.14	N/A	ns
		XQ6SLX75	N/A	N/A	2.25/0.06	2.46/0.53	ns
		XQ6SLX75T	1.80/0.06	N/A	2.25/0.06	N/A	ns
		XQ6SLX150	N/A	N/A	1.79/0.37	1.94/0.94	ns
		XQ6SLX150T	1.43/0.37	N/A	1.79/0.37	N/A	ns

Notes:

1. Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage. These measurements include PLL CLKOUT0 jitter.
2. IFF = Input Flip-Flop or Latch
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 79: **Package Skew *(Cont'd)***

Symbol	Description	Device	Package[2]	Value	Units
$T_{PKGSKEW}$	Package Skew[1]	LX45	CSG324	70	ps
			CS(G)484	99	ps
			FG(G)484	109	ps
			FG(G)676	138	ps
		LX45T	CSG324	75	ps
			CS(G)484	100	ps
			FG(G)484	95	ps
		LX75	CS(G)484	101	ps
			FG(G)484	107	ps
			FG(G)676	161	ps
		LX75T	CS(G)484	107	ps
			FG(G)484	110	ps
			FG(G)676	134	ps
		LX100	CS(G)484	95	ps
			FG(G)484	155	ps
			FG(G)676	144	ps
		LX100T	CS(G)484	88	ps
			FG(G)484	111	ps
			FG(G)676	147	ps
			FG(G)900	134	ps
		LX150	CS(G)484	84	ps
			FG(G)484	103	ps
			FG(G)676	115	ps
			FG(G)900	121	ps
		LX150T	CS(G)484	83	ps
			FG(G)484	88	ps
			FG(G)676	141	ps
			FG(G)900	120	ps

Notes:

1. These values represent the worst-case skew between any two SelectIO resources in the package: shortest delay to longest delay from Pad to Ball.
2. Some of the devices are available in both Pb and Pb-free (additional G) packages as standard ordering options. See DS160: *Spartan-6 Family Overview* for more information.

Table 80: **Sample Window**

Symbol	Description	Device[1]	Speed Grade				Units
			-3	-3N	-2	-1L	
T_{SAMP}	Sampling Error at Receiver Pins[2]	All	510	510	530	740	ps
T_{SAMP_BUFIO2}	Sampling Error at Receiver Pins using BUFIO2[3]	All	430	430	450	590	ps

Notes:

1. LXT devices are not available with a -1L speed grade.
2. This parameter indicates the total sampling error of Spartan-6 FPGA DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the DCM to capture the DDR input registers' edges of operation. These measurements include:
   - CLK0 DCM jitter
   - DCM accuracy (phase offset)
   - DCM phase shift resolution

   These measurements do not include package or clock tree skew.
3. This parameter indicates the total sampling error of Spartan-6 FPGA DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the BUFIO2 clock network and IODELAY2 to capture the DDR input registers' edges of operation. These measurements do not include package or clock tree skew.